



www.sot23.com.tw

Product Summary

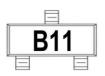
Parameter		Value	Unit
V _{DS}		-30	V
R _{DS(on)} (Typ)	V _{GS} = -10V	60	,
	V _{GS} = -4.5V	85	mΩ
Q_g		10	nC

Package and Pin Configuration

SOT-23



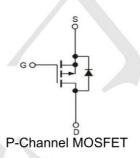
Marking:



Application

- Load/Power Switching
- Interfacing Switching
- Logic Level Shift

Circuit diagram



Absolute Maximum Ratings (T_A=25 ℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	-30	V	
Gate-Source Voltage	V _{GS}	±20	V	
Continuous Drain Current (Note 1)	I _D	-3	Α	
Pulsed Drain Current (Note 2)	I _{DM}	-12	Α	
Continuous Source Current (Diode Conduction)	Is	-1.7	Α	
T _a = 25°C	Б	1.25	١٨/	
Power Dissipation $T_a = 75^{\circ}C$	P _D	0.8	W	
Operating Junction Temperature	Junction Temperature T _J		°C	
Storage Temperature Range	T _{STG}	-50 to +150	°C	





P-Channel Enhancement Mode MOSFET

www.sot23.com.tw

Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Case	R _{eJC}	75	°C/W
Thermal Resistance - Junction to Ambient	R _{OJA}	130	°C/W

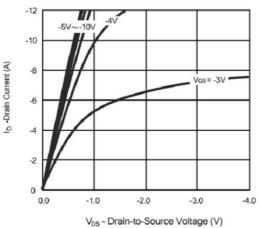
Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V$, $I_D = -250\mu A$	BV _{DSS}	-30			V
Dunin Course On State Besistance	$V_{GS} = -10V, I_{D} = -3A$	Б	/	60	90	mΩ
Drain-Source On-State Resistance	$V_{GS} = -4.5V$, $I_{D} = -2A$	$R_{DS(ON)}$		75	110	mΩ
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	V _{GS(TH)}	-1		-3	V
Zero Gate Voltage Drain Current	$V_{DS} = -30V, V_{GS} = 0V$	I _{DSS}			-1.0	μΑ
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
Forward Transconductance (Note 4)	$V_{DS} = -10V, I_{D} = -6A$	9 _{fs}		5		S
Diode Forward Voltage	$I_S = -1.7V, V_{GS} = 0V$	V _{SD}			-1.2	V
Dynamic		Λ				
Total Gate Charge (Note 3,4)		Qg		10	15	nC
Gate-Source Charge (Note 3,4)	$V_{DS} = -15V, I_D = -3A,$ $V_{GS} = -10V$	Q _{gs}		1.9		
Gate-Drain Charge (Note 3,4)	V _{GS} 10V	Q_{gd}		2		
Input Capacitance		C _{iss}		565		
Output Capacitance	$V_{DS} = -30V, V_{GS} = 0V,$ f = 1.0MHz	C _{oss}		126		pF
Reverse Transfer Capacitance	- 1 - 1.0IVID2	C _{rss}		75		
Switching				200		
Turn-On Delay Time (Note 3,4))		t _{d(on)}		10	20	
Turn-On Rise Time (Note 3,4)	$V_{DD} = -15V, R_L = 15\Omega,$	t _r		9	20	
Turn-Off Delay Time (Note 3,4)	$I_D = -1A$, $V_{GEN} = -10V$, $R_G = 6\Omega$	t _{d(off)}		27	50	ns
Turn-Off Fall Time (Note 3,4)	$ R_{\rm G}$ $ 0\Omega$ 2	t _f		7	16	

www.sot23.com.tw



Typical Electrical and Thermal Characteristics



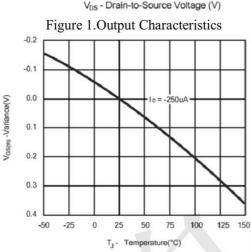


Figure 3. Gate Threshold Variation with Temperatures

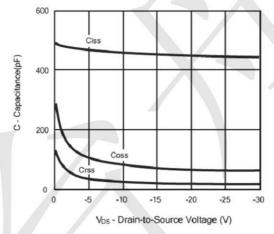


Figure 5. Capacitance Variation with. Drain-source Voltage

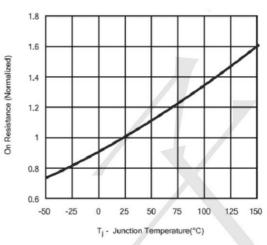


Figure 2.On-Resistance Variation with Temperature

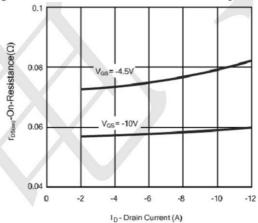


Figure 4.On-Resistance Variation with Drain Current

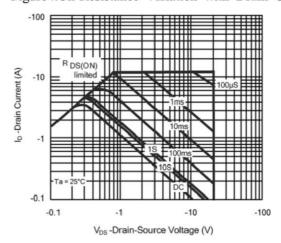
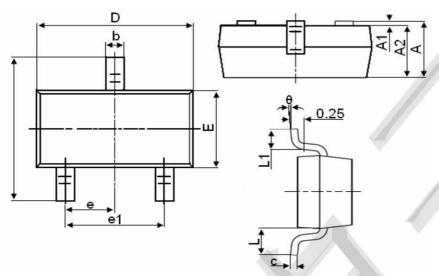


Figure 6. Maximum Safe Operating Area

www.sot23.com.tw



SOT-23 Package Information



Symbol	Dimensions in Millimeters		
	MIN.	MAX.	
A	0.900	1.150	
A1	0.000	0.100	
A2	0.900	1.050	
b	0.300	0.500	
С	0.080	0.150	
D	2.800	3.000	
E	1.200	1.400	
E1	2.250	2.550	
е	0.950TYP		
e1	1.800	2.000	
L	0.550REF		
L1	0.300	0.500	
θ	0°	8°	

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by TECH PUBLIC manufacturer:

Other Similar products are found below:

MCH3443-TL-E MCH6422-TL-E FDPF9N50NZ NTNS3A92PZT5G IRFD120 JANTX2N5237 2N7000 2SK2464-TL-E AOD464 2SJ277-DL-E 2SK2267(Q) 2SK2545(Q,T) 405094E 423220D MIC4420CM-TR VN1206L 614234A 715780A SSM6J414TU,LF(T 751625C IRS2092STRPBF-EL IPS70R2K0CEAKMA1 BSF024N03LT3 G PSMN4R2-30MLD TK31J60W5,S1VQ(O 2SK2614(TE16L1,Q) DMN1017UCP3-7 EFC2J004NUZTDG P85W28HP2F-7071 DMN1053UCP4-7 NTE2384 NTE2969 NTE6400A DMC2700UDMQ-7 DMN2080UCB4-7 DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7 SSM6P54TU,LF DMP22D4UFO-7B IPS60R3K4CEAKMA1 DMN1006UCA6-7 DMN16M9UCA6-7 STF5N65M6 IRF40H233XTMA1 IPSA70R950CEAKMA1 IPSA70R2K0CEAKMA1 STU5N65M6 C3M0021120D DMN6022SSD-13